

SEMICONDUCTOR TECHNICAL DATA

KTC3875S

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION. SWITCHING APPLICATION.

FEATURES

· Excellent hFE Linearity

: $h_{FE}(0.1mA)/h_{FE}(2mA)=0.95(Typ.)$.

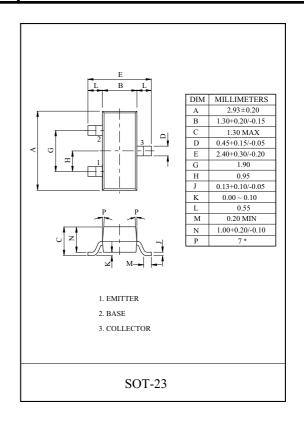
· High h_{FE} : h_{FE} =70 ~ 700.

· Low Noise: NF=1dB(Typ.), 10dB(Max.).

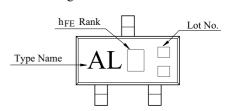
· Complementary to KTA1504S.

MAXIMUM RATING (Ta=25℃)

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CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	V _{CBO}	60	V	
Collector-Emitter Voltage	V _{CEO}	50	V	
Emitter-Base Voltage	V _{EBO}	5	V	
Collector Current	I_{C}	150	mA	
Base Current	I_{B}	30	mA	
Collector Power Dissipation	$P_{\rm C}$	150	mW	
Junction Temperature	T _j	150	$^{\circ}$ C	
Storage Temperature Range	T_{stg}	- 55 ∼150	$^{\circ}$ C	



Marking

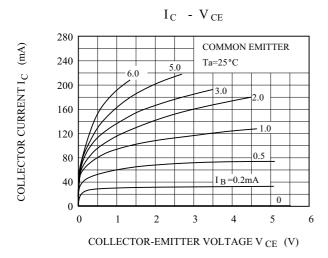


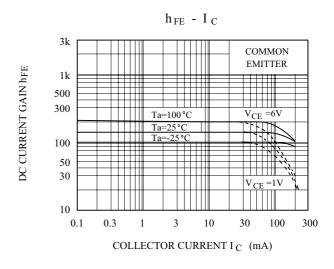
ELECTRICAL CHARACTERISTICS (Ta=25 °C)

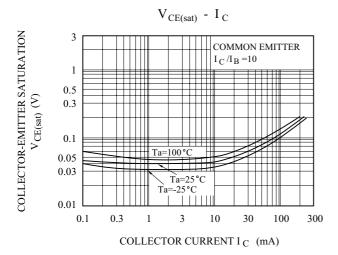
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	$V_{CB} = 60V, I_{E} = 0$	-	-	0.1	μA
Emitter Cut-off Current	I _{EBO}	$V_{EB}=5V$, $I_{C}=0$	-	-	0.1	μA
DC Current Gain	h _{FE} (Note)	$V_{CE}=6V$, $I_{C}=2mA$	70	-	700	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_{C}=100 \text{mA}, I_{B}=10 \text{mA}$	-	0.1	0.25	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	$I_{C}=100 \text{mA}, I_{B}=10 \text{mA}$	-	0.86	1.0	V
Transition Frequency	f_{T}	$V_{CE}=10V$, $I_{C}=1mA$	80	-	-	MHz
Collector Output Capacitance	C _{ob}	V_{CB} =10V, I_E =0, f=1MHz	-	2.0	3.5	pF
Noise Figure	NF	V_{CE} =6V, I_{C} =0.1mA f=1kHz, Rg =10k Ω	-	1.0	10	dB

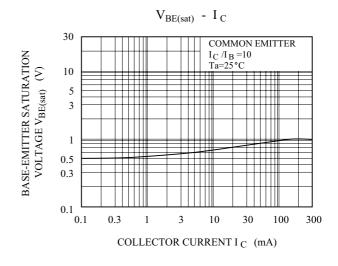
Note: h_{FE} Classification O:70 ~140, Y:120 ~240, GR(G):200 ~400, BL(L):350 ~700

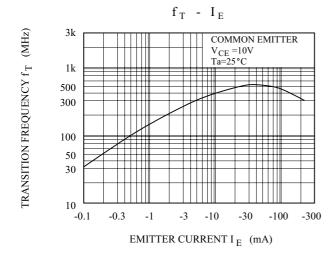
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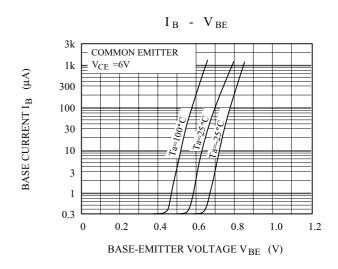






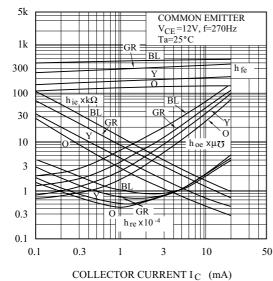






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h PARAMETER

h PARAMETER - V_{CE}

